The RF Line NPN Silicon

High-Frequency Transistor

... designed for amplifier, oscillator or frequency multiplier applications in industrial equipment. Suitable for use as a Class A, B or C output driver or pre-driver stages in VHF and UHF.

- · Low Cost SORF Plastic Surface Mount Package
- Guaranteed RF Specification |S₂₁|²
- · S-Parameter Characterization
- Tape and Reel Packaging Options Available by adding suffix:

R1 suffix = 500 units per reel

R2 suffix = 2,500 units per reel

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	VCEO	30	Vdc
Collector-Base Voltage	V _{CBO}	40	Vdc
Emitter-Base Voltage	V _{EBO}	3.5	Vdc
Collector Current — Continuous	lc	400	mAdc
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

DEVICE MARKING

MRF5943 = 5943

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation @ T _A = 25°C Derate above 25°C	PD	1.0 8.0	Watt mW/°C
Storage Temperature	T _{stg}	150	°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	125	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

	Characteristic	Symbol	Min	Тур	Max	Unit			
:	OFF CHARACTERISTICS								
(Collector-Emitter Breakdown Voltage (IC = 5.0 mA)	V _(BR) CEO	30	_	_	٧			
1	Collector-Base Breakdown Voltage (I _C = 100 μA)	V _(BR) CBO	40	_	_	٧			
	Emitter-Base Breakdown Voltage (I _E = 100 μA)	V _{(BR)EBO}	3.5	_	_	٧			
	Collector Cutoff Current (V _{CE} = 20 V)	ICEO	_	_	50	μΑ			
	Collector Cutoff Current (V _{CB} = 15 V)	Ісво	_	_	10	μΑ			

ON CHARACTERISTICS

DC Current Gain ($I_C = 50 \text{ mA}, V_{CE} = 15 \text{ V}$)	hFE	25	_	300	_
Collector–Emitter Saturation Voltage ($I_C = 100 \text{ mA}, I_B = 10 \text{ mA}$)	V _{CE(sat)}	_	_	0.2	V
Base–Emitter Saturation Voltage (I _C = 100 mA, I _B = 10 mA)	V _{BE(sat)}	_	_	1.0	V

SMALL-SIGNAL CHARACTERISTICS

Current-Gain — Bandwidth Product (IC = 35 mA, V _{CE} = 15 V, f = 100 MHz)	fΤ	_	1550	_	MHz
Insertion Gain (V _{CE} = 15 V, I _C = 35 mA, f = 250 MHz)	S ₂₁ ²	12	15	_	dB

REV 6

MRF5943, R1, R2

I_C = 400 mA SURFACE MOUNT HIGH-FREQUENCY TRANSISTOR NPN SILICON



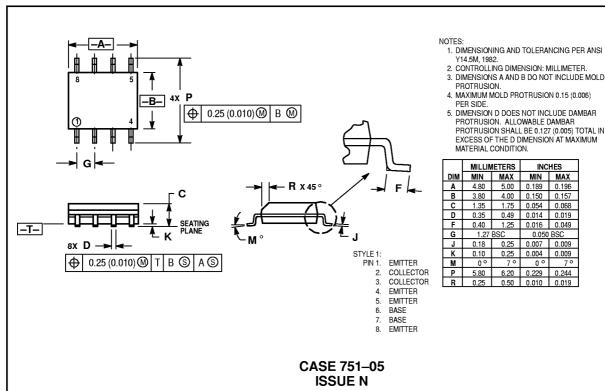
CASE 751-05, STYLE 1 (SO-8)



VCE	lc	f	S ₁₁		S ₂₁		S ₁₂		s ₂₂	
(Volts)	(mA)	(MHz)	S ₁₁	ф	S ₂₁	ф	S ₁₂	ф	S ₂₂	ф
15	35	10	0.37	-63	53.7	157	0.01	59	0.91	-18
		30	0.52	-120	36.5	128	0.01	48	0.64	-38
		50	0.58	-142	25.4	113	0.02	45	0.47	-44
		70	0.59	-154	19	105	0.02	46	0.38	-44
		100	0.60	-162	13.6	97	0.02	49	0.32	-43
		300	0.64	178	4.6	77	0.05	59	0.28	-49
		500	0.65	168	2.8	64	0.07	60	0.32	-62
		700	0.65	159	2.0	53	0.09	63	0.38	-76
		1000	0.64	144	1.4	38	0.13	63	0.46	-93

Table 1. Common Emitter S-Parameters

PACKAGE DIMENSIONS



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